

Voltage controlled filter

FEATURES

- voltage controllable frequency 12 octave range
- voltage controllable resonance from zero to oscillation
- accurate exponential frequency scale
- accurate linear resonance scale
- low control voltage feedthrough -45dB typical
- filter configurable into LPF, HPF, all pass, etc.
- low noise: -86dB typical
- low distortion in passband 0.1% typical
- low warm up drift
- configurable into low distortion voltage controlled sine wave oscillator
- improved CEM3320 replacement

AS3320 AS3320F PDIP-18 QFN-24 4x4mm 0,5mm

General Description

The AS3320 is a high performance voltage controlled four-pole filter with on-chip voltage controllable resonance IC. The four independent sections may be interconnected to provide a wide variety of filter responses, such as low pass, high pass, band pass and all pass. A single input exponentially controls the frequency over greater than a ten octave range with little control voltage feedthrough. Another input controls the resonance in a modified linear manner from zero to low distortion oscillation. For those demanding applications, provision has been made to allow trimming for improved control voltage rejection. Each filter section features a variable gain cell which is fully temperature compensated, exhibits a better signal-to-noise ratio and generates its low distortion predominantly in the second harmonic. The device includes a minus two volt regulator to ensure low power dissipation and consequent low warm-up drift.

PDIP-18	QFN-24L	Pin	Description	
Pin No	Pin No	Name	Description	
1	4	IN1	Input Stage 1	
2	5	IN2	Input Stage 2	
3	7	GND	Ground	
4	8	Cap2	Capacitor Stage 2	
5	9	Cap1	Capacitor Stage 1	
6	11	Out2	Output Stage 2	
7	12	Out1	Output Stage 1	
8	14	Vres	Resonance Input	
9	15	Ires	Resonance Control Input	
10	16	Out4	Output Stage 4	
11	17	Cap4	Capacitor Stage 4	
12	19	V_{CFI}	Voltage Control Frequency Input	
13	20	Vee	Negative power	
14	22	Vcc	Positive power	
15	23	Out3	Output Stage 3	
16	24	Cap3	Capacitor Stage 3	
17	2	IN3	Input Stage 3	
18	3	IN4	Input Stage 4	
-	Power pad	Power pad	Don't connect	

Pin Information

Circuit Block and Connection Diagram (PDIP-18)



Absolute Maximum Ratings

Voltage between Vcc and Vee pins Voltage between Vcc and GND pins Voltage between Vee and GND pins Voltage between Cell Input and GND pins Voltage between Frequency Control and GND pins Voltage between Resonance Control and GND pins Current through any pin Storage Temperature Range Operating Temperature Range +22V, -0,5V +18V, -0,5V -4V, -0,5V +0,5V, -6V ±6V +2V, -18V ±40mA - 55°C to 150°C - 25°C to 75°C



AS "ALFA RPAR" Joint Stock Company ALFA Riga, Latvia www.alfarzpp.lv; alfa@alfarzpp.lv

Electrical Characteristics

V_{CC} =+15V R _F = 100K T _A = 25°C				
Parameter	Min.	Тур.	Max.	Units
Gain of Variable Gain Cell at V _{CFI} =0	0.7	1	1,3	
Input Bias Current of Frequency Control Input	0.2	1	1.5	μΑ
Input Impedance of Resonance Signal Input	2.7	3.6	4.5	KΩ
Output Swing At Clipping	10	12	14	V.P.P.
Output voltage DC ¹	5	6.5	9	V
Buffer Input Bias Current	±10	±30	±100	nA
Buffer Output Impedance ²	25	50	100	Ω
Voltage at the negative supply pin ³	-2.4	-2.7	-2.9	V
Positive Supply Current, I _{CC}	3.8	5	6.5	mA
Negative Supply Current, IEE ³	8	8.4	8.8	mA

Typical Electrical Characteristics

Parameter	Min.	Тур.	Max.	Units
Pole Frequency Control Range ⁴	3500:1	10,000:1	-	
Sensitivity of Pole Frequency Control Scale, Midrange	57.5	60	62.5	mV/decade
Tempco of Pole Frequency Control Scale	3000	3300	3600	ppm
Exponential Error of Pole Frequency Control Scale ⁵	-	4	12	%
Max Gain of Variable Gain Cell	2.4	3	3.6	
Tempco of Variable Gain Cell ⁶	-	500	1500	ppm
Output Impedance of Gain Cell ⁶	0.5	1	2	MΩ
Pole Frequency Control Feedthrough	-	60	200	mV
Pole Frequency Warm-up Drift	-	0.5	1.5	%
Gm of Resonance Control Element at Icr=100µA	0.8	1	1.2	mmhos
Amount of Resonance Obtainable Before Oscillation	20	30	-	dB
Resonance Control Feedthrough ⁷	-	0.2	1,5	V
Output Noise re Max Output ⁸	-76	-86	-	dB
Rejection in Bandreject	73	83	-	dB
Distortion in Passband ^{9,11}	-	0.1	0.3	%
Distortion in Bandreject ^{10,11}	-	0.3	1	%
Distortion of Sine Wave Oscillation ¹²	-	0.5	1.5	%
Internal Reference Current, IREF	45	63	85	μΑ
Buffer Slew Rate	1.5	3	-	V/µS
Buffer Sink Capability	0.4	0.5	0.63	mA
Positive Supply Range, V _{CC}	+9	-	+18	V
Negative Supply Range, V _{EE} ³	-4	-	-18	V

Note 1: V_{IN} = 0, R_{C} = 91K $\Omega,~R_{F}$ = 100K Ω Note 2: V_{CFI} = 0

Note 3: Current limiting resistor always required. $R_{EE} = (1.5 \div 2.2)K\Omega$

Note 4: -20mV < V_{CFI} < +160mV

- **Note 5:** $-16mV < V_{CFI} < +176mV$. Most of this error occurs in upper two octaves.
- **Note 6:** V_{CFI} = 0

Note 7: Untrimmed. 0 < ICR < 100µA

Note 8: Filter is connected as low pass and set for 20 KHz cut-off frequency.

Note 9: Output signal is 3dB below clipping point.

Note 10: Output signal is 3dB below passband level, which is 3dB below clipping point. In general, this is worst case condition.

Note 11: Distortion is predominantly second harmonic.

Note 12: Sinewave is not clipped by first stage.

Specifications subject to change without notice.



Device type	Documentation	Package
AS3320	CKEH.431146.001	PDIP-18
AS3320F	CKEH.431146.001	QFN-24L

Package Information

PDIP-18 (300MIL)







QFN-24 4x4 mm 0.5 mm



0,11(2.7) EXPOSED PAD 7 12 000000 0,02(0.4)(24x) 6 0,11(2.7) € 0,01min(0.2) Þ € Ē 18 CHAMFERED CORNER FOR PIN 1 IDENTIFICATION 19 0.3X0.3 0,01(0.23)(24x) 0,02typ.(0.5)

BOTTOM VIEW

SIDE VIEW-2

SEATING PLANE

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	1101	n	hict	orv/
ne:	/151	CJEE	11151	UIV
		••••		•••

Date	Revision	Changes
05-Oct-2016	1	Short version 1
09-Jan-2017	2	QFN-24L – new package
20-Mar-2017	3	Drawing and typical electrical characteristics updated
09-May-2017	4	Block circuit and typical electrical characteristics updated
29-May-2017	5	Minor changes